

Product Overview

FDB1D7N10CL7: Power MOSFET, N-Channel, Standard Gate, 100 V, 268 A, 1.7 mΩ

For complete documentation, see the data sheet.

This N-Channel MV MOSFET is produced using ON Semiconductor's advanced Power Trench process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

Features

- Low Qrr
- Soft recovery body diode
- Low RDS(on)
- Small Footprint (5 x 6 mm)
- RoHS compliant

Applications

- Motor Control
- DC-DC Converters
- Battery Management
- Solar Inverters

Benefits

- Minimize switching loss
- Reduced EMI and voltage spike
- Minimize conduction loss
- Compact design

End Products

- Fork Lifts, Multi Rotor Drones, Power Tools
- Power Supplies
- Battery Packs and Chargers
- Power Optimizers

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{(BR)DSS} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q ₃ Typ @ V _{GS} = 4.5 V (nC)	Q ₃ Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
FDB1D7N10CL7	3.7388	Pb-free Halide free	Active	N-Channel	Single	100	±20	4	268	250	-	-	1.75	-	116	8285	D2P AK-7 / TO-263-7

For more information please contact your local sales support at www.onsemi.com.

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